

## 1. Scope

The present specifications shall apply to FMB-2306.

## 2. Outline

## High Frequency Rectification

Type	Silicon Schottky Barrier Diode
Structure	Resin Molded
Applications	High Frequency Rectification,etc

## 3. Flammability

UL94V-0(Equivalent)

## 4. Absolute maximum ratings

No.	Item	Symbol	Unit	Rating	Conditions
1	Transient Peak Reverse Voltage	$V_{RSM}$	V	60	
2	Peak Reverse Voltage	$V_{RM}$	V	60	
3	Average Forward Current	$I_{F(AV)}$	A	30	Refer to Derating of 7
4	Peak Surge Forward Current	$I_{FSM}$	A	150	10msec. Half sinewave, one shot
5	$I^2t$ Limiting Value	$I^2t$	$A^2s$	112	$1msec \leq t \leq 10msec$
6	Junction Temperature	$T_j$	$^{\circ}C$	-40~+150	
7	Storage Temperature	$T_{stg}$	$^{\circ}C$	-40~+150	

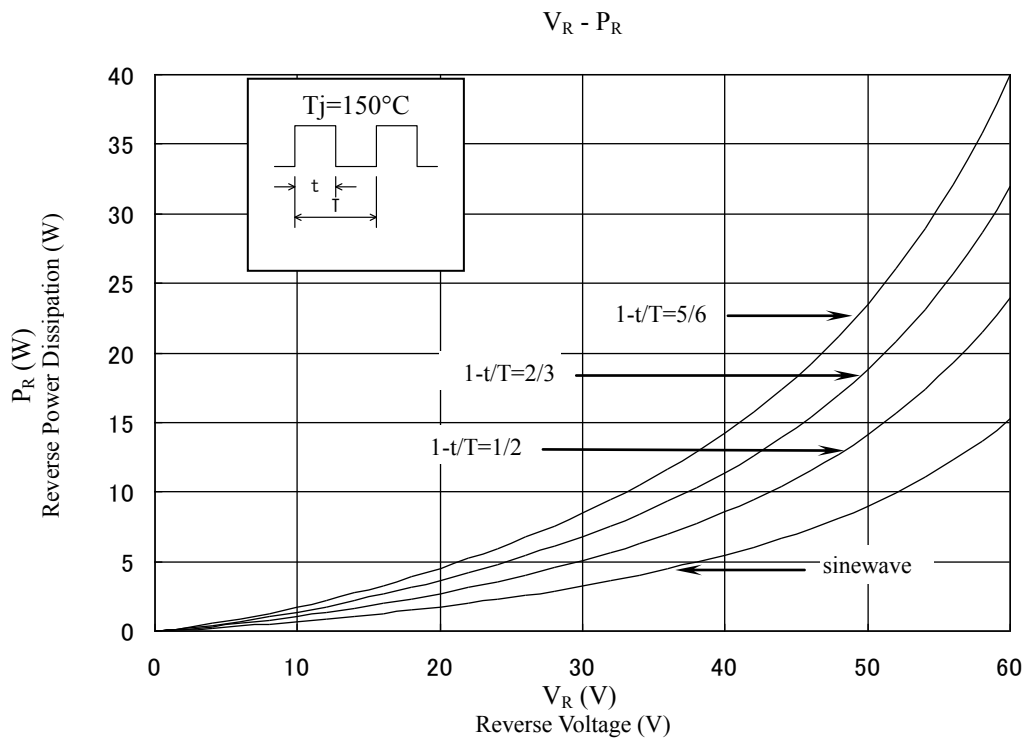
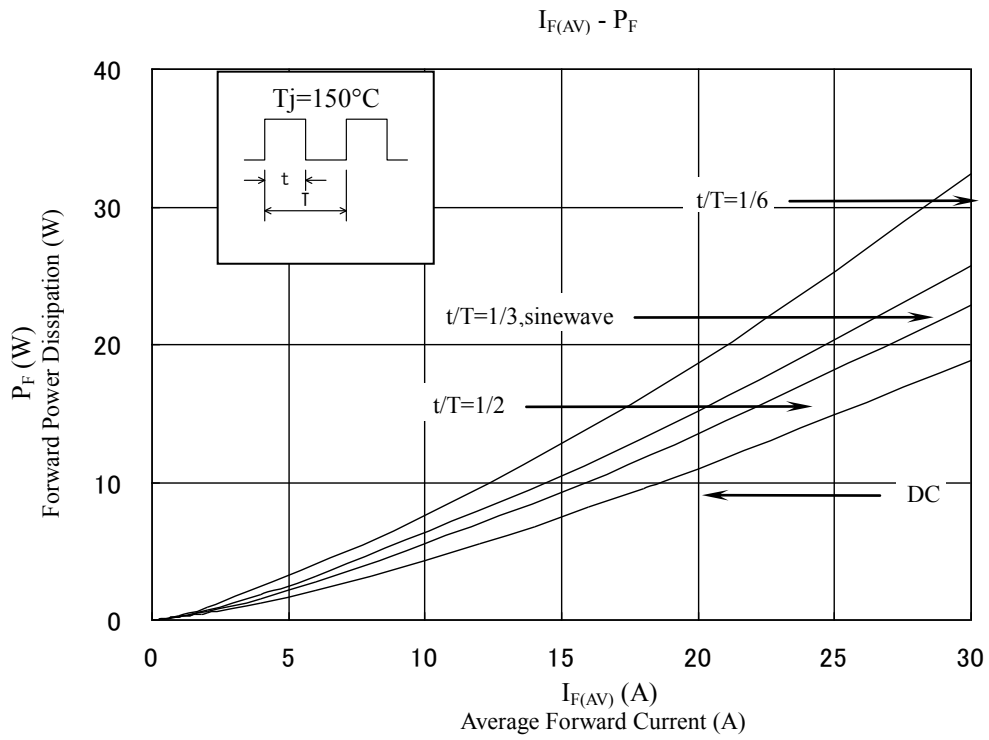
No.1,2,4,5 show ratings per one chip.

## 5. Electrical characteristics (Ta=25°C, unless otherwise specified)

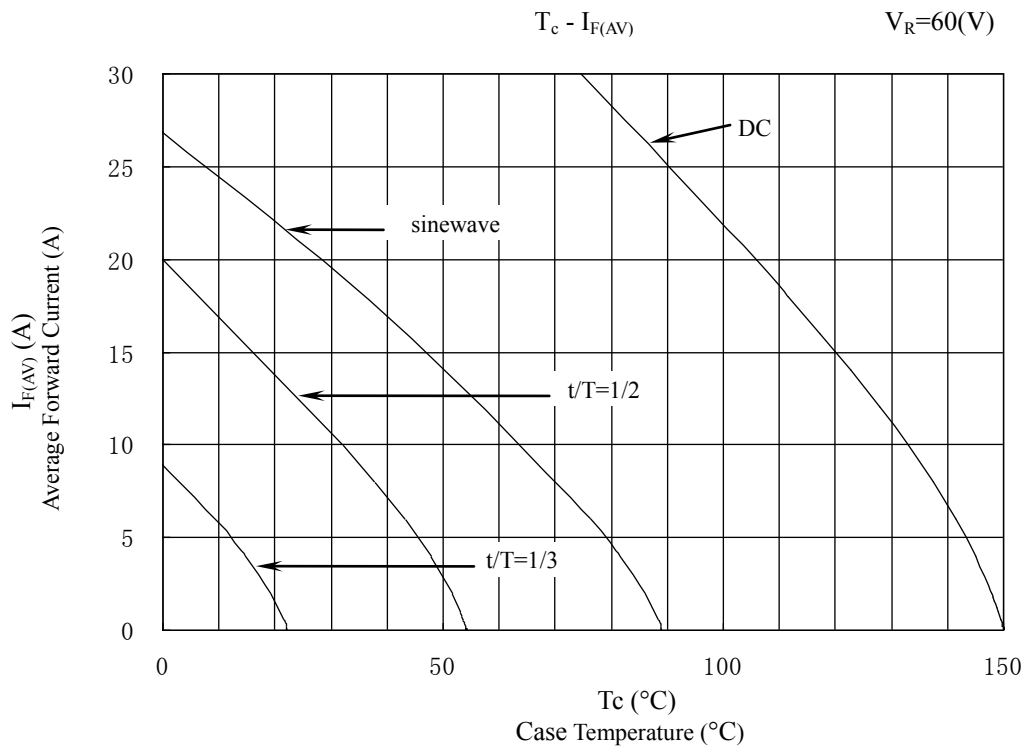
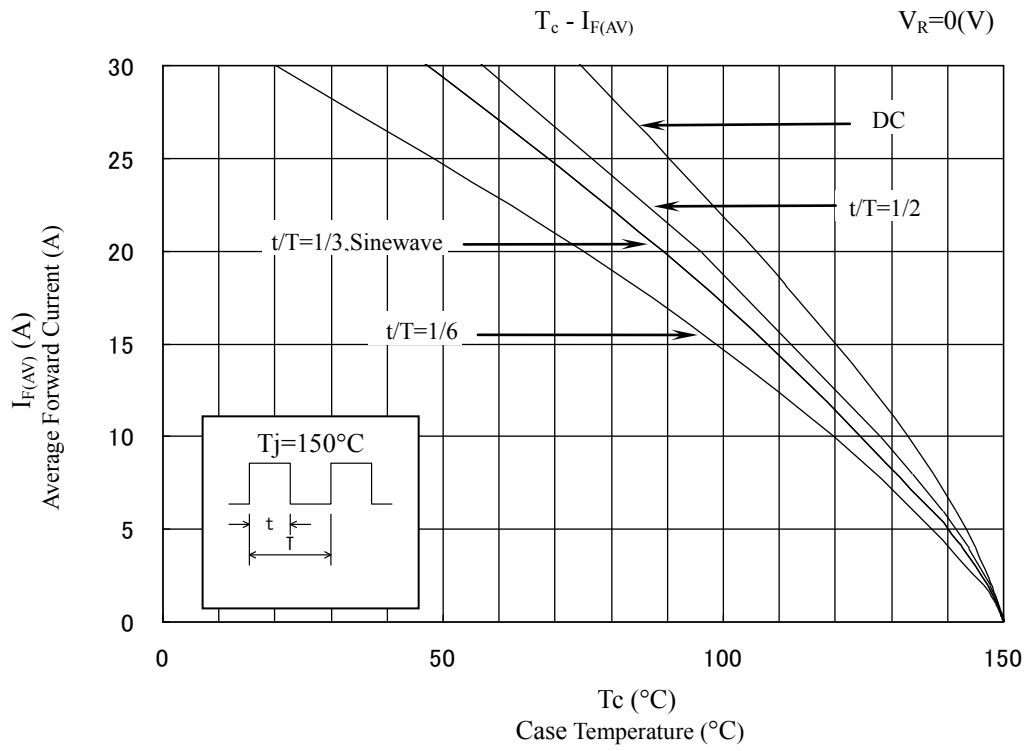
No.	Item	Symbol	Unit	Value	Conditions
1	Forward Voltage Drop	$V_F$	V	0.7 max.	$I_F=15A$
2	Reverse Leakage Current	$I_R$	mA	8 max.	$V_R=V_{RM}$
3	Reverse Leakage Current Under High Temperature	$HI_R \cdot 1$	mA	115 max.	$V_R=V_{RM}, T_j=125^{\circ}C$
		$HI_R \cdot 2$	mA	400 max.	$V_R=V_{RM}, T_j=150^{\circ}C$
4	Thermal Resistance	$R_{th(j-c)}$	$^{\circ}C/W$	4.0 max.	Between Junction and case

No.1,2,3 show characteristics per one chip.

6. Characteristics

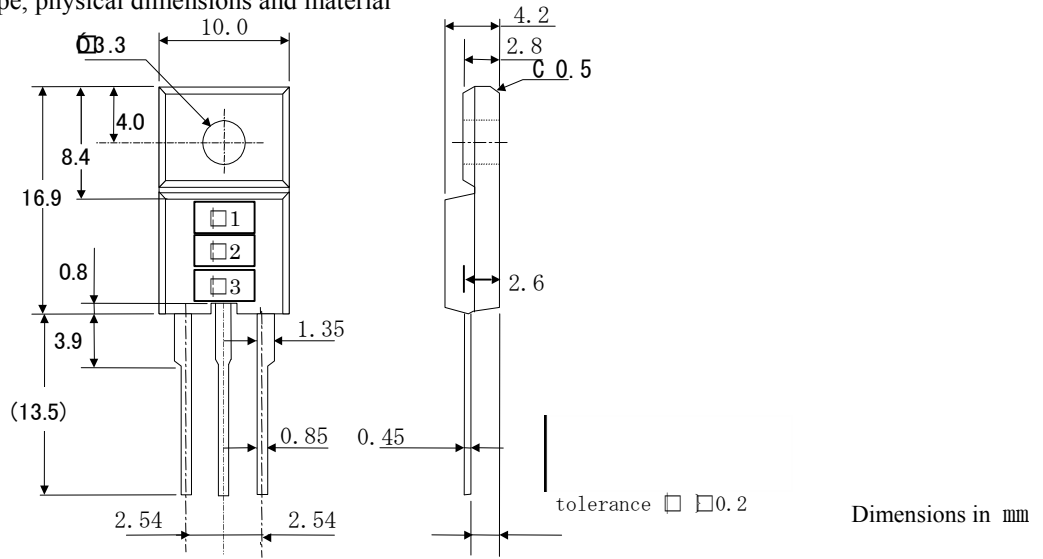


7. Derating



8. Package information

8-1 Package type, physical dimensions and material



8-2 Appearance

The body shall be clean and shall not bear any stain, rust or flaw.

8-3 Marking

Type Name	Marking		
	*1 Type Name	*2 Polarity	*3 Lot number
FMB-2306	B2306		1st letter: Last digit of year 2nd letter: Month From 1 to 9 for Jan. to Sep., O for Oct., N for Nov., D for Dec. 3rd & 4th letter: Day ex. 3D24 (December 24, 2003)